

## Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N5339J)
- JANTX level (2N5339JX)
- JANTXV level (2N5339JV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV
- Radiation testing (total dose) upon request

Please contact Semicoa for special configurations  
[www.SEMICOA.com](http://www.SEMICOA.com) or (714) 979-1900

## Applications

- General purpose switching transistor
- Low power
- NPN silicon transistor



## Features

- Hermetically sealed TO-39 metal can
- Also available in chip configuration
- Chip geometry 9201
- Reference document:  
MIL-PRF-19500/560

## Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Absolute Maximum Ratings		T <sub>C</sub> = 25°C unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	100	Volts
Collector-Base Voltage	V <sub>CB0</sub>	100	Volts
Emitter-Base Voltage	V <sub>EBO</sub>	6	Volts
Collector Current, Continuous	I <sub>C</sub>	5	A
Power Dissipation, T <sub>A</sub> = 25°C Derate linearly above 25°C	P <sub>T</sub>	1 5.71	W mW/°C
Thermal Resistance	R <sub>θJC</sub>	17.5	°C/W
Operating Junction Temperature Storage Temperature	T <sub>J</sub> T <sub>STG</sub>	-65 to +200	°C

**ELECTRICAL CHARACTERISTICS**

characteristics specified at  $T_A = 25^\circ\text{C}$

Off Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50 \text{ mA}$	100			Volts
Collector-Base Cutoff Current	$I_{CBO}$	$V_{CB} = 100 \text{ Volts}$			10	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{CEO}$	$V_{CE} = 100 \text{ Volts}$			100	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{CEX1}$	$V_{CE} = 90 \text{ Volts}, V_{BE} = 1.5 \text{ Volts}$			10	$\mu\text{A}$
	$I_{CEX2}$	$V_{CE} = 90 \text{ Volts}, V_{BE} = 1.5 \text{ Volts}, T_A = 150^\circ\text{C}$			10	mA
Emitter-Base Cutoff Current	$I_{EBO}$	$V_{EB} = 6 \text{ Volts}$			100	$\mu\text{A}$

On Characteristics			Pulse Test: Pulse Width = 300 $\mu\text{s}$ , Duty Cycle $\leq 2.0\%$			
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{FE1}$	$I_C = 0.5 \text{ A}, V_{CE} = 2 \text{ Volts}$	60		240	
	$h_{FE2}$	$I_C = 2 \text{ A}, V_{CE} = 2 \text{ Volts}$	60			
	$h_{FE3}$	$I_C = 5 \text{ A}, V_{CE} = 2 \text{ Volts}$	40			
	$h_{FE4}$	$I_C = 2 \text{ A}, V_{CE} = 2 \text{ Volts}, T_A = -55^\circ\text{C}$	12			
Base-Emitter Saturation Voltage	$V_{BEsat1}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			1.2	Volts
	$V_{BEsat2}$	$I_C = 5 \text{ A}, I_B = 500 \text{ mA}$			1.8	
Collector-Emitter Saturation Voltage	$V_{CEsat1}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			0.7	Volts
	$V_{CEsat2}$	$I_C = 5 \text{ A}, I_B = 500 \text{ mA}$			1.2	

Dynamic Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 10 \text{ Volts}, I_C = 500 \text{ mA}, f = 10 \text{ MHz}$	3		15	
Open Circuit Output Capacitance	$C_{OBO}$	$V_{CB} = 10 \text{ Volts}, I_E = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			250	pF
Open Circuit Input Capacitance	$C_{IBO}$	$V_{EB} = 2 \text{ Volts}, I_C = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			1,000	pF

Switching Characteristics						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Delay Time	$t_d$	$I_C = 2 \text{ A}, I_{B1} = 200 \text{ mA}$			100	ns
Rise Time	$t_r$				100	
Storage Time	$t_s$	$I_C = 2 \text{ mA}, I_{B1} = I_{B2} = 200 \text{ mA}$			2	$\mu\text{s}$
Fall Time	$t_f$				200	